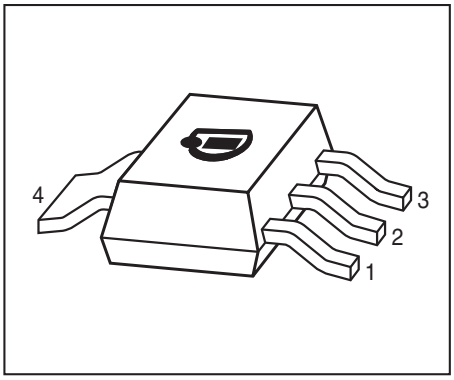
NPN Silicon High-Voltage Transistors



- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary type: PZTA92 (PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

Type	Marking	Pin Configuration						Package
PZTA42	PZTA42	1=B	2=C	3=E	4=C	-	-	SOT223

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	300	V
Collector-base voltage	V_{CBO}	300	
Emitter-base voltage	V_{EBO}	6	
Collector current	I_C	500	mA
Base current	I_B	100	
Total power dissipation- $T_S \leq 124$ °C	P_{tot}	1.5	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	≤ 17	K/W

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

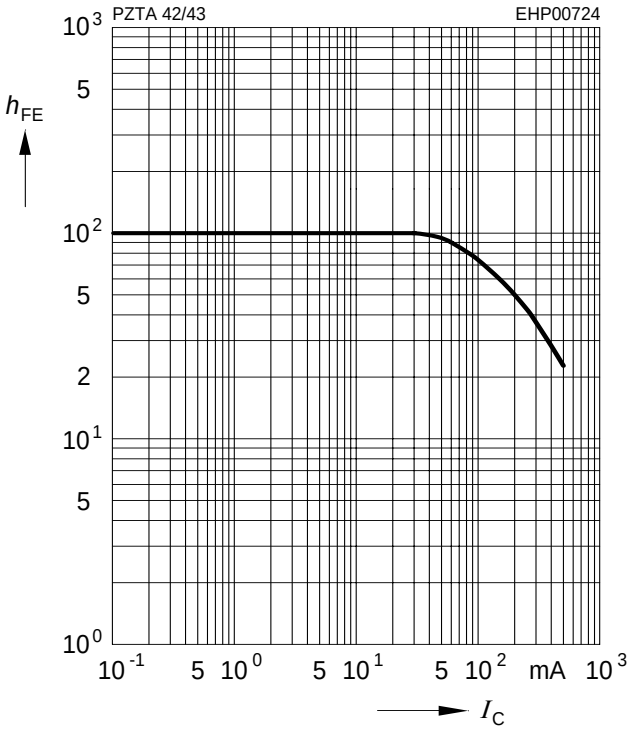
Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	300	-	-	V
Collector-base breakdown voltage I_C = 100 µA, I_E = 0	$V_{(BR)CBO}$	300	-	-	
Emitter-base breakdown voltage I_E = 100 µA, I_C = 0	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current V_{CB} = 200 V, I_E = 0 V_{CB} = 200 V, I_E = 0 , T_A = 150 °C	I_{CBO}	 - -	 - -	 0.1 20	µA
Emitter-base cutoff current V_{EB} = 5 V, I_C = 0	I_{EBO}	-	-	100	nA
DC current gain[1)] I_C = 1 mA, V_{CE} = 10 V I_C = 10 mA, V_{CE} = 10 V I_C = 30 mA, V_{CE} = 10 V	h_{FE}	 25 40 40	 - - -	 - - -	-
Collector-emitter saturation voltage[1)] I_C = 20 mA, I_B = 2 mA	V_{CEsat}	-	-	0.5	V
Base emitter saturation voltage[1)] I_C = 20 mA, I_B = 2 mA	V_{BEsat}	-	-	0.9	
AC Characteristics					
Transition frequency I_C = 20 MHz, V_{CE} = 10 V, f = 20 MHz	f_T	-	70	-	MHz
Collector-base capacitance V_{CB} = 20 V, f = 1 MHz	C_{cb}	-	-	3	pF

[1]Pulse test: t < 300µs; D < 2%

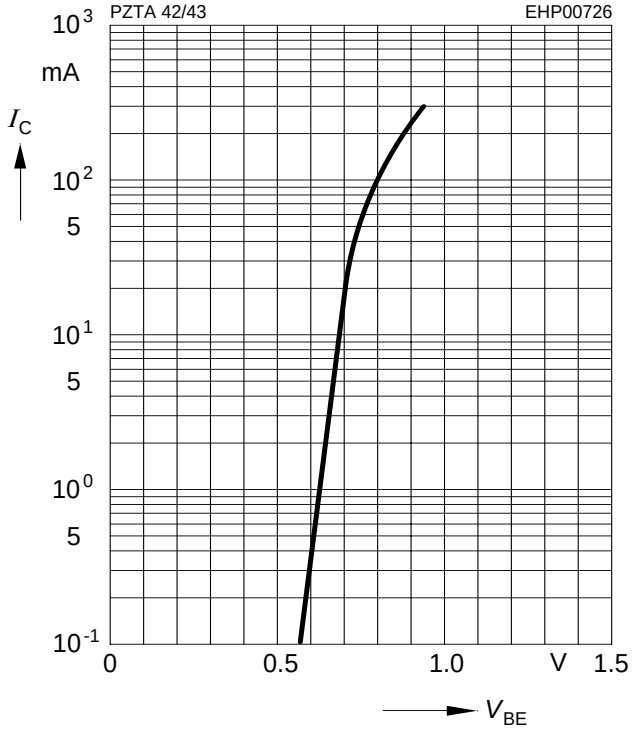
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 10 V



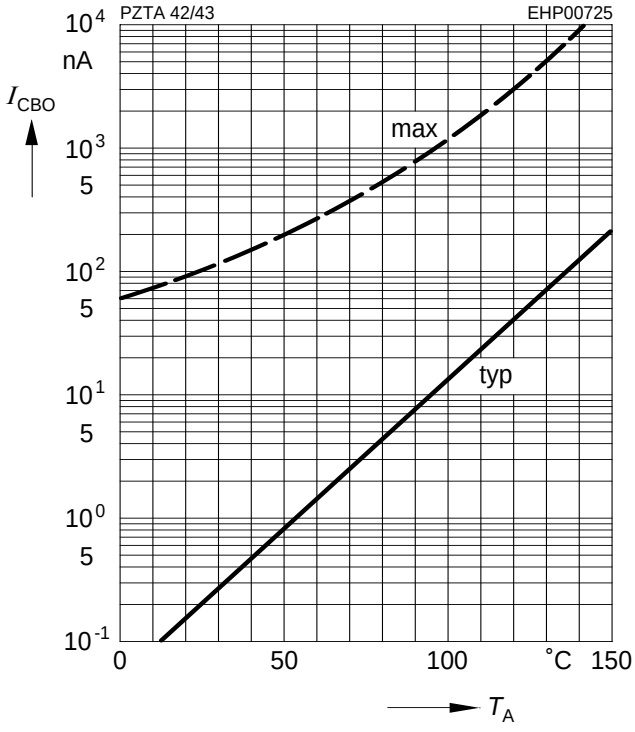
Collector current $I_C = f(V_{BE})$

V_{CE} = 10V



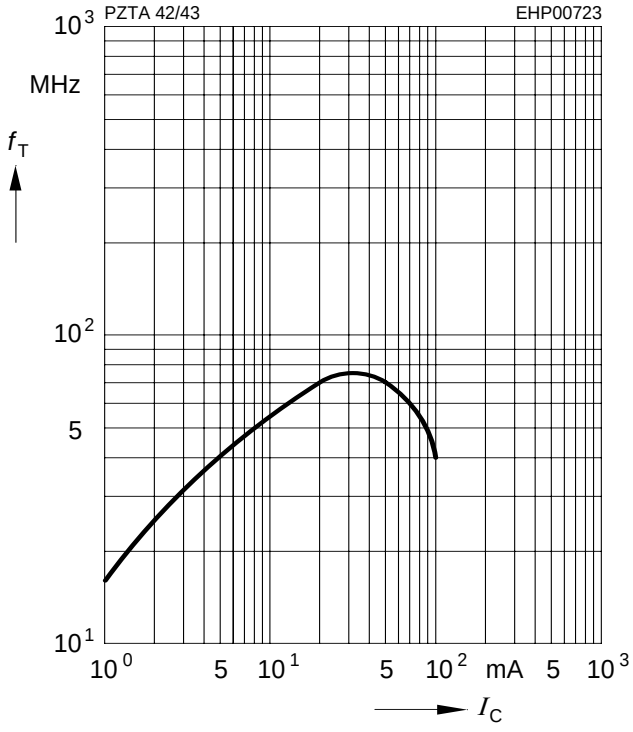
Collector cutoff current $I_{CBO} = f(T_A)$

V_{CB} = 200 V

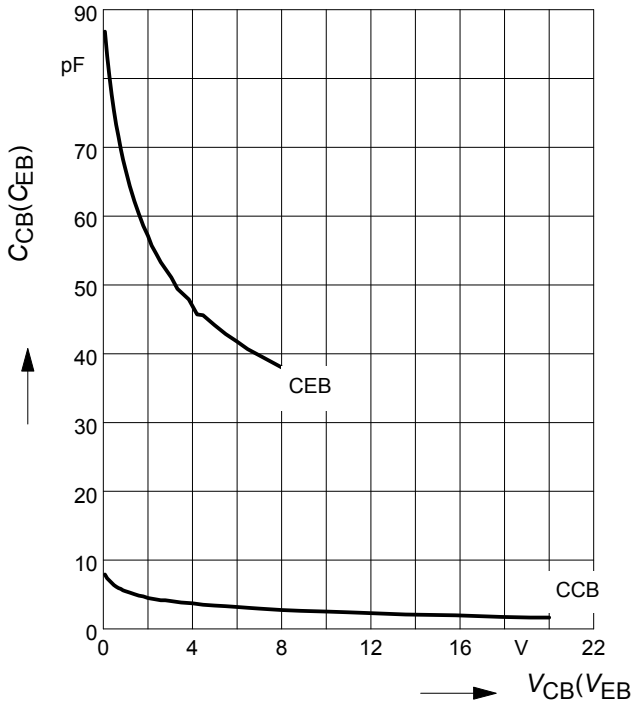


Transition frequency $f_T = f(I_C)$

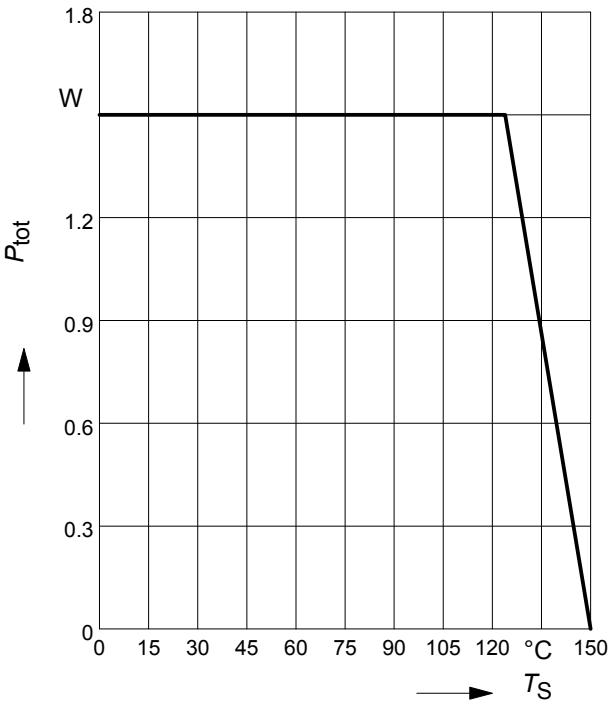
V_{CE} = 10 V



Collector-base capacitance $C_{cb} = f(V_{CB})$
Emitter-base capacitance $C_{eb} = f(V_{EB})$

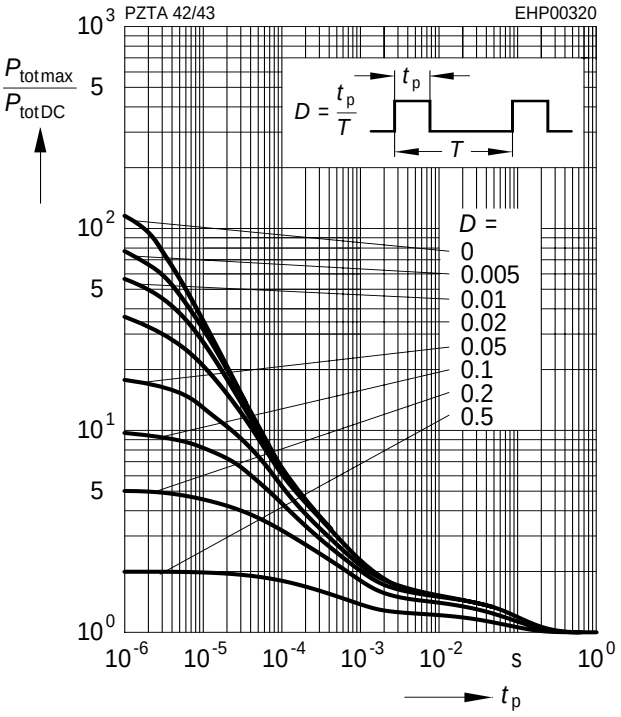


Total power dissipation $P_{tot} = f(T_S)$



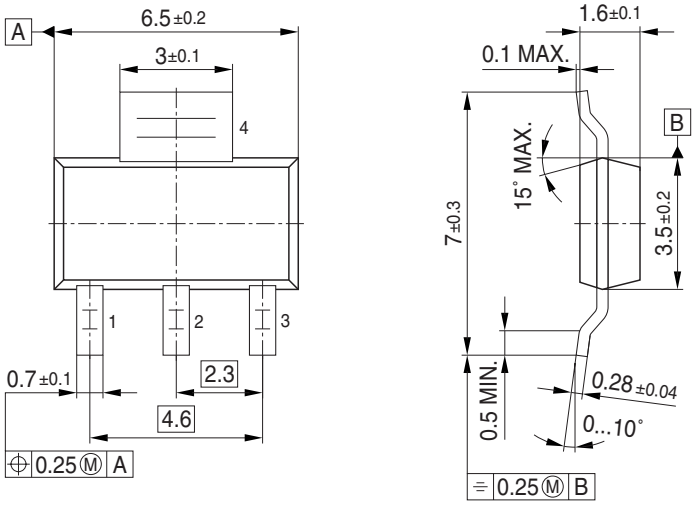
Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

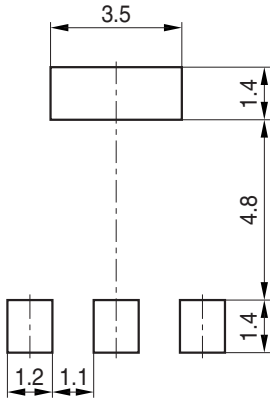


Package Outline

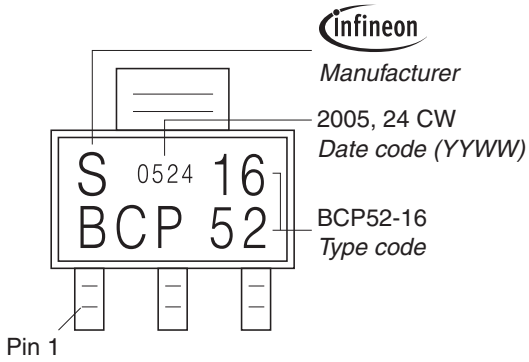




Foot Print

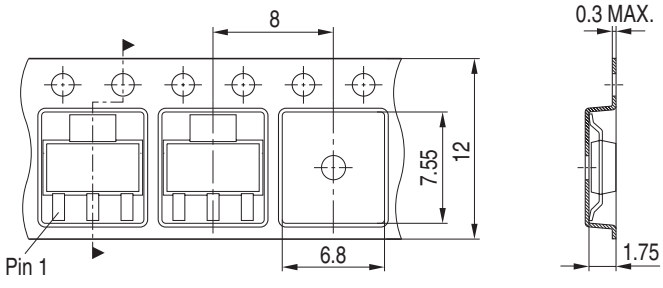


Marking Layout (Example)



Packing

Reel ø180 mm = 1.000 Pieces/Reel
Reel ø330 mm = 4.000 Pieces/Reel



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